

LOGIC LEVEL TRIAC

TO220-F (FULLY ISOLATED CASE)	On-State Current 8 Amp	Gate Trigger Current < 10 mA
	Off-State Voltage 200 V ÷ 800 V	
	This series of TRIACs uses a high performance PNPN technology. These parts are intended for general purpose AC switching applications with highly inductive loads.	

Absolute Maximum Ratings, according to IEC publication No. 134

SYMBOL	PARAMETER	CONDITIONS	Value	Unit
$I_{T(RMS)}$	RMS On-state Current (full sine wave)	All Conduction Angle, $T_C = 95^\circ\text{C}$	8	A
I_{TSM}	Non-repetitive On-State Current	Full Cycle, 60 Hz ($t = 16.7\text{ ms}$)	88	A
I_{TSM}	Non-repetitive On-State Current	Full Cycle, 50 Hz ($t = 20\text{ ms}$)	80	A
I^2t	Fusing Current	$t_p = 10\text{ ms}$, Half Cycle	32	A ² s
I_{GM}	Peak Gate Current	$20\ \mu\text{s max.}$ $T_j = 125^\circ\text{C}$	4	A
$P_{G(AV)}$	Average Gate Power Dissipation	$T_j = 125^\circ\text{C}$	1	W
di/dt	Critical rate of rise of on-state current	$I_G = 2x I_{GT}$, $t_r \leq 100\text{ns}$ $f = 120\text{ Hz}$, $T_j = 125^\circ\text{C}$	50	A/ μs
T_j	Operating Temperature		(-40 +125)	$^\circ\text{C}$
T_{stg}	Storage Temperature		(-40 +150)	$^\circ\text{C}$
T_{sld}	Soldering Temperature	10s max	260	$^\circ\text{C}$
V_{iso}	R.M.S. isolation voltage 50/60 Hz sinusoidal waveform		2.500	Vac

SYMBOL	PARAMETER	VOLTAGE					Unit
		B	D	M	S	N	
V_{DRM}	Repetitive Peak Off State Voltage	200	400	600	700	800	V
V_{RRM}							

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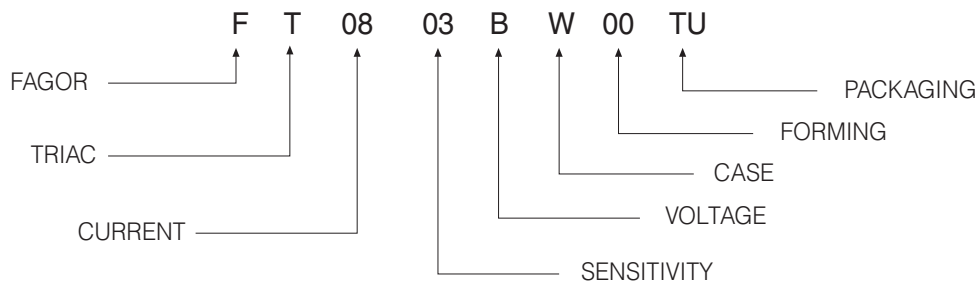
Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	Quadrant		SENSITIVITY				Unit
					03	07	08	09	
$I_{GT}^{(1)}$	Gate Trigger Current	$V_D = 12 V_{DC}, R_L = 33\Omega, T_j = 25^\circ C$	Q1÷Q3	MAX	3	5	10	10	mA
			Q4	MAX	5	7		10	mA
V_{GT}	Gate Trigger Voltage	$V_D = 12 V_{DC}, R_L = 33\Omega, T_j = 25^\circ C$	Q1÷Q3	MAX	1.3				V
			Q1÷Q4	MAX	1.3				V
V_{GD}	Gate Non Trigger Voltage	$V_D = V_{DRM}, R_L = 3.3K\Omega, T_j = 125^\circ C$	Q1÷Q3	MIN	0.2				V
			Q1÷Q4	MIN	0.2				V
$I_H^{(2)}$	Holding Current	$I_T = 100 \text{ mA}, \text{ Gate open}, T_j = 25^\circ C$		MAX	7	15	15	20	mA
I_L	Latching Current	$I_G = 1.2 I_{GT}, T_j = 25^\circ C$	Q1, Q3	MAX			25		mA
			Q1,Q3,Q4	MAX	7	20		20	mA
			Q2	MAX	20	30	30	25	mA
$dv/dt^{(2)}$	Critical Rate of Voltage Rise	$V_D = 0.67 \times V_{DRM}, \text{ Gate open}, T_j = 125^\circ C$		MIN	10	20	40	50	V/ μs
$(di/dt)^c^{(2)}$	Critical Rate of Current Rise	$(dv/dt)^c = 0.1 \text{ V}/\mu s, T_j = 125^\circ C$		MIN	1.2	3.5	5.4	2.5	A/ms
				MIN	0.6	1.5	2.8	1.5	A/ms
				MIN					
$V_{TM}^{(2)}$	On-state Voltage	$I_T = 11 \text{ Amp}, t_p = 380 \mu s, T_j = 25^\circ C$		MAX	1.55				V
$V_{I(O)}^{(2)}$	Threshold Voltage	$T_j = 125^\circ C$		MAX	0.85				V
$r_d^{(2)}$	Dynamic Resistance	$T_j = 125^\circ C$		MAX	60				m Ω
I_{DRM}/I_{RRM}	Off-State Leakage Current	$V_D = V_{DRM}, T_j = 125^\circ C$ $V_R = V_{RRM}, T_j = 25^\circ C$		MAX	1				mA
				MAX	5				μA
$R_{th(j-c)}$	Thermal Resistance Junction-Case	for AC 360° conduction angle			3.5				°C/W
$R_{th(j-a)}$	Thermal Resistance Junction-Ambient	$S = 1 \text{ cm}^2$			50				°C/W

(1) Minimum I_{GT} is guaranteed at 5% of I_{GT} max.

(2) For either polarity of electrode MT2 voltage with reference to electrode MT1.

PART NUMBER INFORMATION



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Fig. 1: Maximum power dissipation versus RMS on-state current (full cycle).

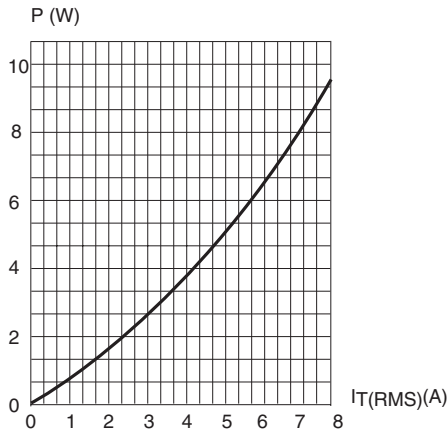


Fig. 2: RMS on-state current versus case temperature (full cycle).

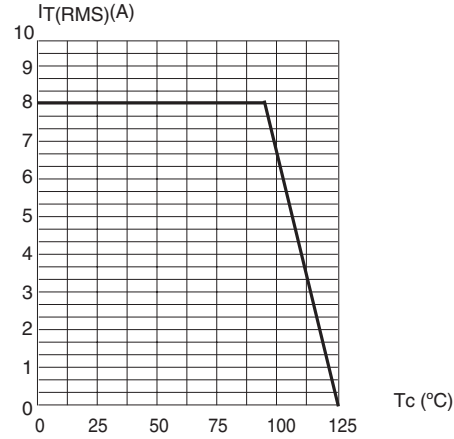


Fig. 3: Relative variation of thermal impedance versus pulse duration.

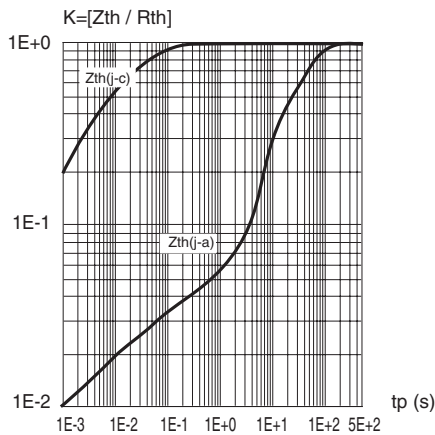


Fig. 4: On-state characteristics (maximum values)

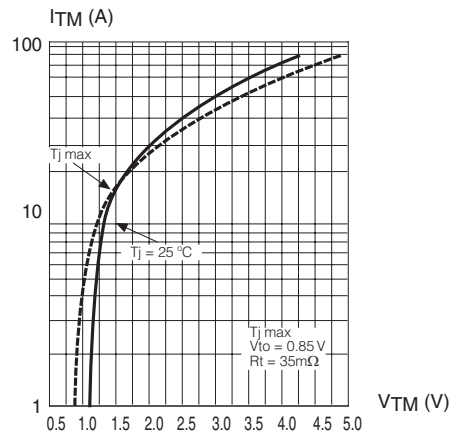


Fig. 5: Surge peak on-state current versus number of cycles

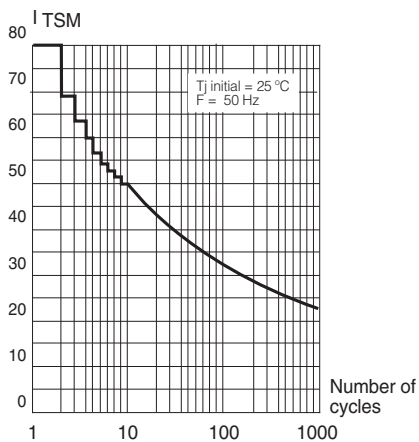
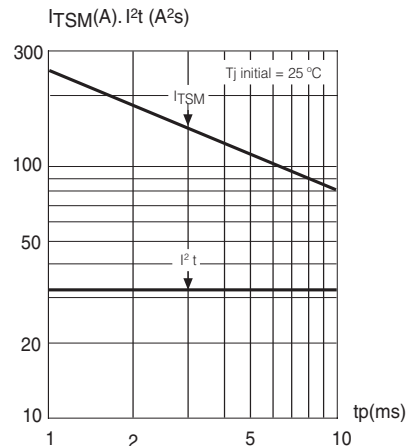


Fig. 6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10ms, and corresponding value of I²t.



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Fig. 7: Relative variation of gate trigger current, holding current and latching versus junction temperature (typical values)

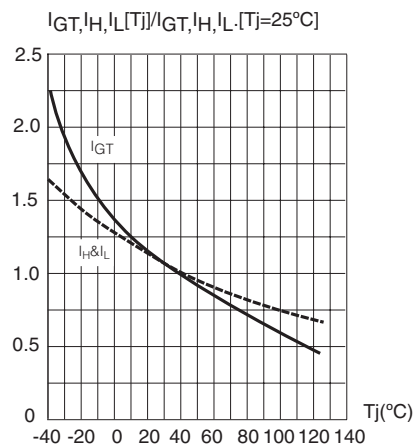


Fig. 8: Relative variation of critical rate of decrease of main current versus junction temperature

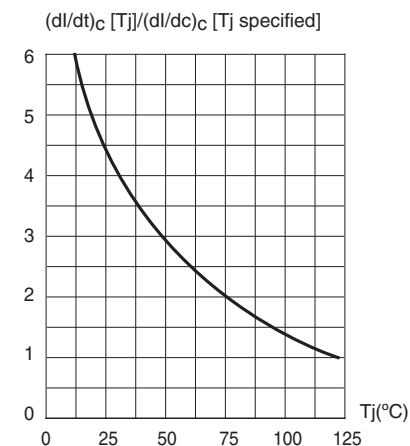
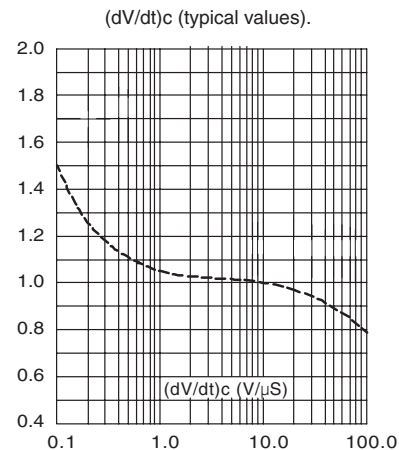


Fig. 9: Relative variation of critical rate of decrease of main current versus



PACKAGE MECHANICAL DATA TO220-F

